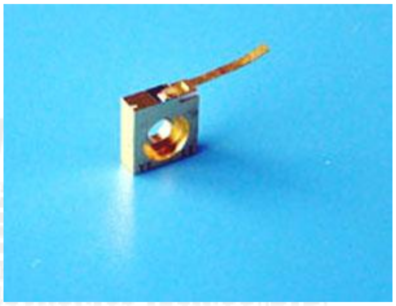
808nm Laser Diode

■ Features

Output Power: 1000mW (CW)

Efficient Quantum Well Structure

Standard C-Mount Package



■ Absolute Maximum Ratings

(Tc=25℃)

Item	Symbol	Absolute Maximum Ratings	Unit
Optical Output Power	Po	1000	mW
LD Reverse Voltage	Vr (LD)	2	V
Storage Temperature	Tstg	-10~60	℃
Operating Case Temperature	Tc	0~35	℃

■ Initial Electrical/Optical Characteristics

(Tc=25℃)

Item	**Symbol**	**Typ.**	**Unit**
Optical Output	Po	1000	mW
Peak Wavelength*	λp	808±5	nm
Threshold Current	Ith	≤0. 24	A
Operating Current	Iop	≤1. 24	A
Slope Efficiency	η	≥1. 0	W/A
Operating Voltage	Vop	≤2. 0	V
Horizontal Beam Divergence	θ//	≤10	deg.
Vertical Beam Divergence	θ⊥	≤38	deg.
Wavelength Temperature Coefficient		0. 3	nm/℃
Polarization		TE	

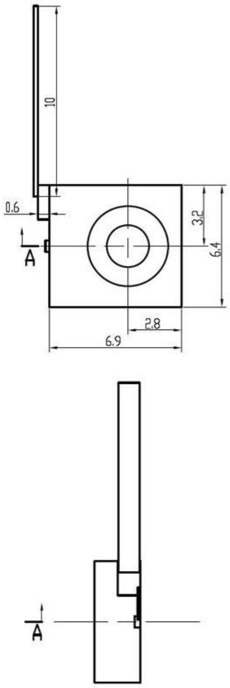
* Measuring specifications.

All figures in this specification are measured by CNI’s method and may contain measurement deviations

The above specifications are for reference purpose only and subjected to change without prior notice.

Outline Dimension

C-Mount Package



(Unit: mm)

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